

W20080124 PCT/US 24 JAN 2008

Form PTO 1449		ATTY. DOCKET NUMBER HIRA.0217	SERIAL NUMBER To be Assigned
U.S. Department of Commerce Patent and Trademark Office		APPLICANT SUDA et al.	
Information Disclosure Statement by Applicant		FILING DATE Concurrently Herewith	GROUP

U.S. Patent Documents

Examiner Initial	DOCUMENT NUMBER	DATE	NAME	CLASS	Sub Class	FILING DATE
	5,900,648	5/4/99	Harris et al.			3/28/97

Foreign Patent Documents

Examiner Initial	DOCUMENT NUMBER	FILING DATE	COUNTRY	CLASS	Sub Class	TRANSLATION	
						YES	NO
	2000-150792	11/11/98	Japan			Abstract	X
	2001-094099	9/21/99	Japan			Abstract	X
	2002-246594	12/21/2001	Japan			Abstract	X
	FR 2 707 425	7/9/93	France			Abstract	X

Other Documents (Including Author, Title, Date Pertinent Pages, Etc.)

	International Search Report of PCT/JP2004/010696 mailed November 9, 2004	
	James Kolodzey et al., "Electrical Conduction and Dielectric Breakdown in Aluminum Oxide Insulators on Silicon", IEEE Transactions on Electron Devices, Vol. 47, No. 1, January 2000, pp. 121-128	
	N. Onojima et al., "Heteroepitaxial Growth of Insulating AlN on 6H-SiC by MBE", Materials Science Forum Vols. 389-393, (2002), pp. 1457-1460	
	N. Onojima et al., "Impact of SiC Surface Control on Initial Growth Mode and Crystalline Quality of AlN Grown by Molecular-Beam Epitaxy", 5 th International Conference on Nitride Semiconductors, May 25-30, 2003, Technical Digest, pp. 28 and 228	
	N. Onojima et al., "Lattice Relaxation Process of AlN Growth on Atomically Flat 6H-SiC Substrate in Molecular Beam Epitaxy", Journal of Crystal Growth (2002), pp. 1012-1016	
	N. Onojima et al., "Molecular-Beam Epitaxial Growth of Insulating AlN on Surface-Controlled 6H-SiC Substrate by HCl Gas Etching", Applied Physics Letters, Vol. 80, No. 1, January 7, 2002, pp. 76-78	
	Jun Suda et al., "Effects of 6H-SiC Surface Reconstruction on Lattice Relaxation of AlN Buffer Layers in Molecular-Beam Epitaxial Growth of GaN", Applied Physics Letters, Vol. 81, No. 27, December 30, 2002, pp. 5141-5143	
	N. Onojima et al., "Impact of SiC Surface control on Initial Growth Mode and Crystalline Quality of AlN Grown by Molecular-Beam Epitaxy", Phys. Stat. Sol. No. 7 (2003), pp. 2529-2532	
	N. Onojima et al., "High-Quality AlN by Initial Layer-by-Layer Growth on Surface-Controlled 4H-SiC(0001) Substrate", Jpn. J. Appl. Phys., Vol. 42 (May 1, 2003), pp. L445-L447	
EXAMINER	/Selim Ahmed/	
	DATE CONSIDERED	07/20/2009

EXAMINER: Initial if citation is considered, whether or not citation is in conformance with MPEP 609; draw a line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant